

the second conduction type,

wherein a concentration of an impurity [of] in the semiconductor region of the first conduction type is [almost] substantially equal to a concentration of an impurity [of] in the semiconductor substrate.

Claim 5, line 3, before "the", first occurrence, insert --at least one of--;

line 3, delete "and/or" and insert therefore --and--.

Claim 6, line 3, before "the", first occurrence, insert --at least one of--;

line 3, delete "and/or" and insert therefore --and--.

Claim 7, line 3, before "the", first occurrence, insert --at least one of--;

line 3, delete "and/or" and insert therefore --and--.

REMARKS

The Office Action mailed September 12, 2000 (hereinafter, the "Office Action") has been received and carefully noted. The above amendments and the following remarks are submitted as a full and complete response thereto. Claims 1, and 5-7 have been amended to correct issues of form and place the application in better form for allowance. No new matter has been added and no new issues are raised which require further consideration and/or search. Accordingly, Claims 1-7 are pending in the application and respectfully resubmitted for consideration.

Rejection of Claims 1 and 5-7 under 35 USC § 112:

Claim 1 has been rejected under 35 USC § 112, first paragraph, as allegedly containing subject matter which was not described in the specification in such a way as to